

Silicon Switching Diode

Rev. V1

Features

- Available in JAN, JANTX, and JANTXV per MIL-PRF-19500/116
- Low Capacitance
- · Fast Switching Speed
- Available in Unidirectional, Doubler, Common Anode and Common Cathode Polarities



Maximum Ratings

Operating & Storage Temperature: -65°C to +200°C

Operating Current: 200 mA @ $T_A = +75^{\circ}C$ Derating Factor: 2.0 mA/°C above $T_A = +25^{\circ}C$

Surge Current 2 A (pk)

Electrical Specifications @ $T_A = +25$ °C (unless otherwise specified)

JEDEC TYPE#	V _{BR} @ 100 μA	V_{RWM}	Io	V_{F1} $I_F = 10$ mA dc	V_{F2} $I_F = 100$ mA dc	T _m ¹	I _{R1} @ 20 Vdc	I _{R2} @ 75 Vdc	I _{R3} @ 20 Vdc T _A =150°C	I _{R4} @ 75 Vdc T _A =150°C	Capacitance @ 0 V	Capacitance @1.5 V
	Volts	Volts (pk)	mA	V dc	V dc	nsec	nA	nA	μА	μΑ	pF	pF
1N4148UB	100	75	200	0.8	1.2	5	25	500	35	75	4.0	2.8

1. $C \ge 1 \text{ nF}$, $I_F = I_R = 10 \text{ mA dc}$, $R_L = 100 \Omega$, $\pm 5\%$, $I_{R(REC)} = 1.0 \text{ mA dc}$, $R \ge 1,000 \Omega$

Thermal Characteristics ($T_A = +25$ °C unless otherwise specified)

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Ambient (2)	R _{θJA(PCB)}	325°C/W ⁽⁴⁾
Thermal Resistance, Junction to Solder Pad ⁽³⁾	R _{eJSP}	120°C/W

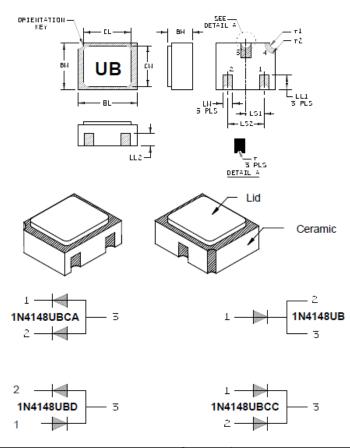
- (2) See figures 11, 12, and 13 of MIL-PRF-19500/116 for thermal impedance curves
- (3) Reuse refers to thermal resistance from junction to the solder pads of the UB package



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Outline Drawing (UB)



		Dime	nsions			Dimensions			
Symbol	Inc	hes	Millimeters		Symbol	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
BH	.046	.056	1.17	1.42	LS ₁	.035	.039	0.89	0.99
BL	.115	.128	2.92	3.25	LS ₂	.071	.079	1.80	2.01
BW	.085	.108	2.16	2.74	LW	.016	.024	0.41	0.61
CL		.128		3.25	R		.008		0.20
CW		.108		2.74	r1		.012		0.31
LL1	.022	.038	0.56	0.97	r2		.022		0.56
LL2	.017	.035	0.43	0.89					

- 1. Dimensions are in inches. Millimeters are given for general information only.
- Ceramic package only.
- 3. Hatched areas on package denote metallized areas. Pad 4 = shielding, connected to the lid.
- In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

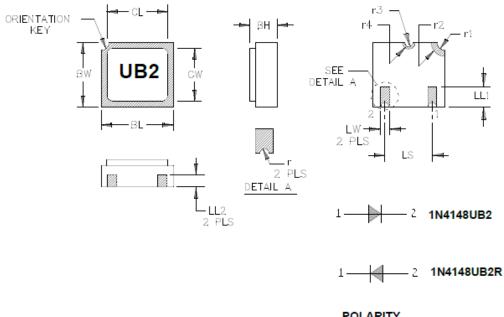
FIGURE 3. Physical dimensions, surface mount (UB versions).



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Outline Drawing (UB2)



POLARITY

		Dime	nsions			Dimensions			
Symbol	Inc	hes	Millimeters		Symbol	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
BH	.046	.056	1.17	1.42	LS	.071	.079	1.80	2.01
BL	.115	.128	2.92	3.25	LW	.016	.024	0.41	0.61
BW	.085	.108	2.16	2.74	r	.008 TYP		0.20 TYP	
CL		.128		3.25	r1	.012 TYP		0.31 TYP	
CW		.108		2.74	r2	.022 TYP		0.56 TYP	
LL1	.022	.038	0.56	0.96	r3	.008 TYP		0.20 TYP	
LL2	.017	.035	0.43	0.89	г4	.012 TYP		0.31 TYP	

- 1. Dimensions are in inches. Millimeters are given for general information only.
- Ceramic package only.
- 3. Hatched areas on package denote metallized areas. Pad 4 = shielding, connected to the lid.
- In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

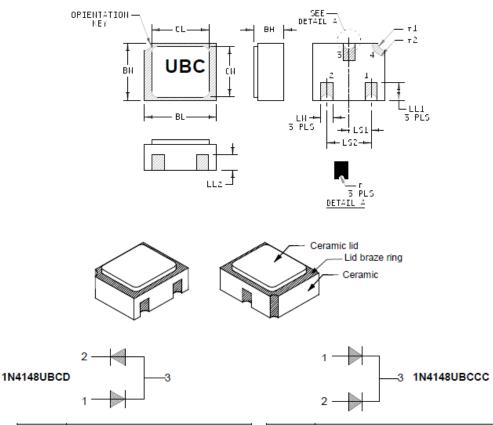
FIGURE 4. Physical dimensions, surface mount (2 pin UB versions).



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Outline Drawing (UBC)



Symbol	Dimensions							
Symbol	Inc	hes	Millimeters					
	Min	Max	Min	Max				
BH	.046	.071	1.17	1.80				
BL	.115	.128	2.92	3.25				
BW	.085	.108	2.16	2.74				
CL		.128		3.25				
CW		.108		2.74				
LL1	.022	.038	0.56	0.96				
LL2	.017	.035	0.43	0.89				

Symbol	Dimensions							
Symbol	Inc	hes	Millimeters					
	Min Max		Min	Max				
LS ₁	.036	.040	0.91	1.02				
LS ₂	.071	.079	1.81	2.01				
LW	.016	.024	0.41	0.61				
r		.008		.203				
r1		.012		.305				
r2		.022		.559				

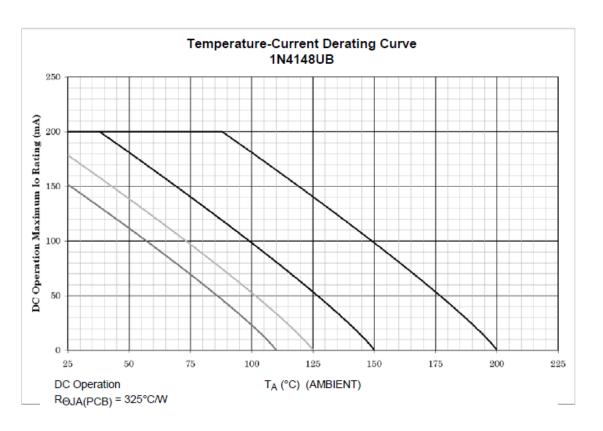
- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. Hatched areas on package denote metallized areas.
- 3. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 4. Pin 4 is connected to lid braze ring.

FIGURE 5. Physical dimensions, surface mount (UBC version, ceramic lid).



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- This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at ≤ T_J specified on this curve. Any parallel line to this curve will intersect the appropriate current for the desired maximum T_J allowed.
- Derate design curve constrained by the maximum junction temperature (T_J ≤ +200°C) and current rating specified. (See 1.3.)
- Derate design curve chosen at T_J ≤ +150°C, where the maximum temperature of electrical test is performed.
- Derate design curves chosen at T_J ≤ +125°C, and +110°C to show current rating where most users want to limit T_J in their application.

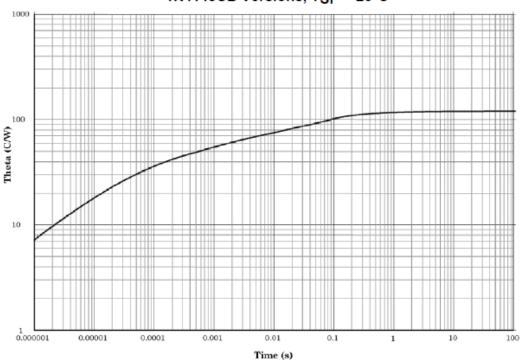
FIGURE 10. Temperature-current derating graph.



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Maximum Thermal Impedance Plots 1N4148UB Versions, TSP = 25°C



R_{0JSP} = 120°C/W

NOTE: $Z_{\theta JX} = 75^{\circ}$ C/W maximum at $t_H = 10$ ms.

FIGURE 13. Thermal impedance (UB versions).



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